

NPN Silicon Epitaxial Planar Transistor**KTC3876****FEATURES**

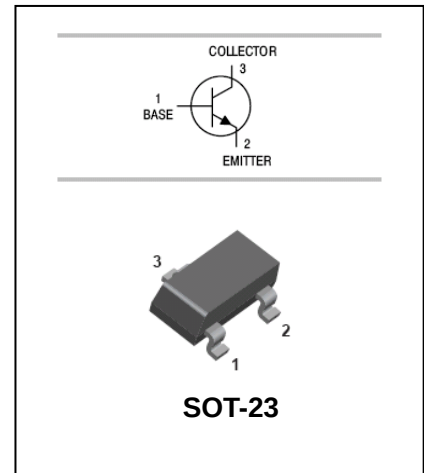
- Complementary To KTA1505.
- Excellent H_{FE} Linearity.
- Low noise.



Lead-free

APPLICATIONS

- General purpose application, switching application.

**ORDERING INFORMATION**

Type No.	Marking	Package Code
KTC3876	WO•/WY•/WG•	SOT-23

MAXIMUM RATING @ $T_a=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	500	mA
P_C	Collector Power Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS @ $T_a=25^{\circ}\text{C}$ unless otherwise specified

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KTC3876

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=35V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=1V, I_C=100mA$	70		400	
		$V_{CE}=6V, I_C=400mA$ O	25			
		Y	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$			0.25	V
Transition frequency	f_T	$V_{CE}=6V, I_C=20mA$		300		MHz
Collector output capacitance	C_{ob}	$V_{CB}=6V, I_E=0, f=1MHz$		7		pF

CLASSIFICATION OF h_{FE}

Rank	O	Y	G
Range	70-140	120-240	200-400
Marking	WO▪	WY▪	WG▪

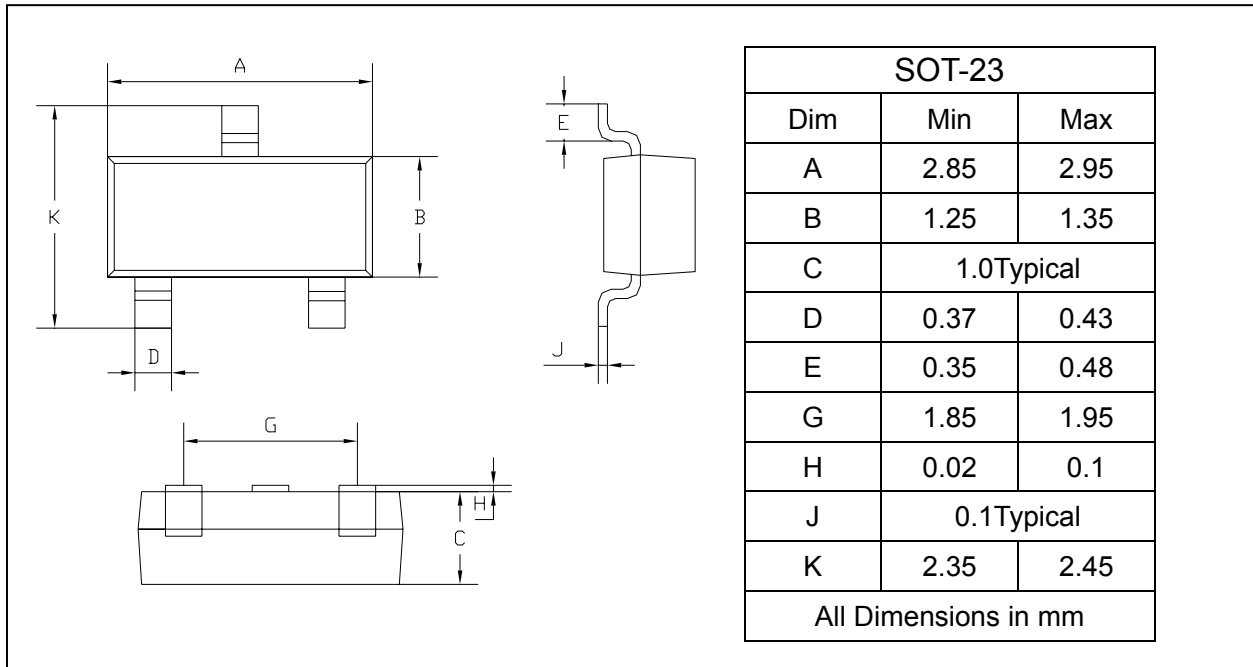
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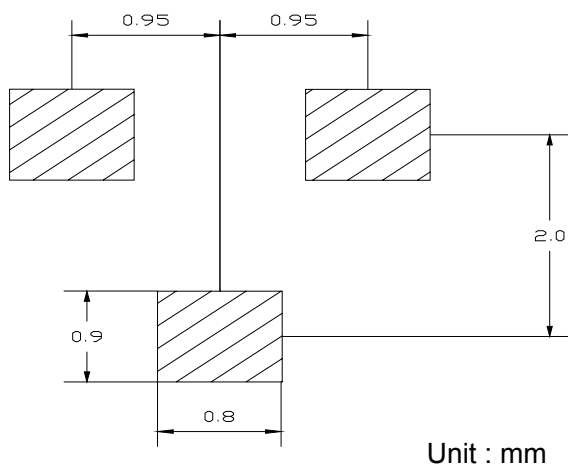
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
KTC3876	SOT-23	3000/Tape&Reel